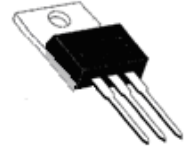




JANTX(V)2N7236

Power MOSFET(P-channel) Transistor



Features:

1. It's voltage control component with good input impedance, small starting power dissipation, wide area of safe operation, good temperature stability.
2. Implementation of standards: QZJ840611
3. Use for high speed switch, circuit of power source contravariance.
4. Quality Class: GS, G.

TECHNICAL DATA:

(Ta = 25°C)

| Parameter name | Symbols | Unit | Specifications | Test Condition |
|-----------------------------------|----------------------|------|----------------|---|
| Drain-Source Voltage | V _{DSS} | V | 100(max.) | |
| Drain Current | I _D | A | 18(max.) | |
| Total Power Dissipation | P _D | W | 125(max.) | (Tc=25°C) |
| Gate-Source Voltage | V _{GSS} | V | ±20(max.) | |
| Junction Temperature | T _{jm} | °C | 150 | |
| Storage Temperature | T _{stg} | °C | -55~+150 | |
| Drain-Source Breakdown Voltage | V _{(BR)OSS} | V | Min.:100 | V _{GS} =0V, I _D =1mA |
| Static Drain-Source On-Resistance | R _{DS(on)} | Ohms | Max.:0.2 | V _{GS} =10V, I _D =9A |
| Gate Threshold Voltage | V _{GS(th)} | V | Min.:2, Max.:4 | V _{DS} = V _{GS} , I _D =1mA |
| Zero Gate Voltage Drain Current | I _{DSS} | uA | Max.:1000 | V _{GS} =0V, V _{DS} =80V |
| Gate-Body Leakage | I _{GSS} | nA | Max.:100 | V _{GS} =±20V, V _{DS} =0V |

Outline and Dimensions: